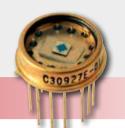
## Avalanche

# Photodiodes

For Analytical Applications

#### **AVALANCHE PHOTODIODES**

Avalanche Photodiodes Si APD Arrays



### Avalanche Photodiodes – Si APD Arrays

#### **Applications**

- Spectroscopy
- Particle detection
- Spot tracking and alignment systems
- · Adaptive optics
- LiDAR (Light Detection And Ranging)

#### **Features and Benefits**

- · High quantum efficiency
- · Hermetically-sealed packages
- Monolithic chip with minimal dead space between elements
- Specific tailored wavelength response
- RoHS compliant
- Customization available upon request

#### **Product Description**

The C30927 series of quadrant Si Avalanche Photodiode utilize the double-diffused "reachthrough" structure. This structure provides ultra-high sensitivity at 400-1000 nm.

The C30927 quadrant structure has a common avalanche junction, with separation of the

quadrants achieved by segmentation of the light entry p+ surface opposite the junction. With this design, there is no dead space between the elements and therefore no loss of response at boresight.

The C30927EH-01, -02 and -03 are optimized for use at wavelengths of 1060, 900, and 800 nm respectively. Each device type will provide high responsivity and excellent performance when operated within about 50 nm of the specified wavelength.

#### Product Table

#### Avalanche Photodiodes - Si APD Arrays

Part Number	Number of Elements	Photo Sensitive Diameter	Responsivity	Dark Current per Element	Spectral Noise Current per Element	Capacitance @ 100 KHz per Element	Response Time	NEP	Operating Voltage
Unit	mm	mm	A/W	nA	pA/√Hz	pF	ns	fW /√Hz)	V
C30927EH-01	4	1.5	15(@ 1060 nm)	25	0.5	1	3	33(@ 1060 nm)	275-425
C30927EH-02	4	1.5	62(@ 900 nm)	25	0.5	1	3	16(@ 900 nm)	275-425
C30927EH-03	4	1.5	55(@ 800 nm)	25	0.5	1	3	9(@ 800 nm)	275 - 425

